

EAST Search History

Ref #	Hits	Search Query	Dbs	Default Operator	Plurals	Time Stamp
S2	43	esd and lcd near panel and (MOS FET MOSFET field near effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:36
S3	2	"20020126430"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:13
S4	7	"6,678,133"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:13
S5	21	("5218222" "5293057" "5336908" "5430602" "5581104" "5654860" "5656967" "5721658" "5744839" "5767552" "5805009" "5880917" "5889644" "5982599" "6004838" "6040733" "6130811" "6137664" "6181540" "6204537" "RE36024").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/18 12:13
S6	1	("6678133").URPN.	USPAT	OR	ON	2005/08/18 12:22
S7	5	esd and (pad line terminal) and protect\$3 near device same impedance near (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:44
S8	5	esd and protect\$3 near device same impedance near (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:47
S9	45	esd and protect\$3 near device same impedance near (small\$3 high\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 09:47

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S10	11	esd and protect\$3 near device same impedance near3 (smaller higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 10:04
S11	11	esd and protect\$3 near device same impedance near3 (smaller higher larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 10:06
S12	52	esd and protect\$3 near device same (impedance resistance) near3 (smaller higher larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:12
S13	1	esd and protect\$3 near device same (impedance resistance) near3 gradually near3 (increas\$3 decreas\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:12
S14	18	esd and (impedance resistance) near3 gradually near3 (increas\$3 decreas\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S15	18	esd and (impedance resistance) near4 gradually near3 (increas\$3 decreas\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S16	18	esd and (impedance resistance) near4 gradually near4 (increas\$3 decreas\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 11:33
S17	36	esd and (impedance resistance) same gradually near3 (increas\$3 decreas\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:08

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S18	15	"6,198,136"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:13
S19	22069	(esd (electrostatic adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:14
S20	1375	S19 same impedance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:15
S21	274	S19 same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:16
S22	4	S21 same compensat\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:18
S23	343	S19 same compensat\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:18
S24	142	S23 same (size length dimension inductance capacitance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 12:19
S25	72	S23 same (size length dimension)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:53

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S26	429	esd and channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:53
S27	133	esd and channel near width same (impedance resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:54
S28	1	esd and channel near width same (impedance resistance) same gradually	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 14:54
S29	30	esd and channel near width same (impedance resistance) same (increase decrease)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 16:37
S30	608	361/91.1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/15 16:37
S31	224	esd and (lead wire) near (impedance resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:27
S32	0	esd and (lead wire) near (impedance resistance) near compensat\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:28
S33	7	esd and (lead wire) near (impedance resistance) near (compensat\$5 chang\$3 modifcat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:31

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S34	9	esd and (lead wire connect\$3) near (impedance resistance) near (compensat\$5 chang\$3 modifcat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:33
S35	13	esd and (lead wire connect\$3) near3 (impedance resistance) near (compensat\$5 chang\$3 modifcat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 09:34
S36	35	esd and (lead wire connect\$3) near3 (impedance resistance) near (match\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 10:18
S37	3	("4455586" "4930644" "5416660"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 09:46
S38	0	("6847511").URPN.	USPAT	OR	ON	2005/11/16 09:49
S39	8	esd and (lead wire connect\$3) near3 (impedance resistance) near (match\$5) and channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 11:24
S40	23	esd and (lead wire connect\$3) with (impedance resistance) with (match\$5) and channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18
S41	145	esd and lcd near panel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:18
S42	7	esd and (lead wire trace) with (impedance resistance) with (match\$5) and channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:19
S43	4	("4719369" "5602494" "6366129" "6642740").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/16 14:36

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S44	2383	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18
S45	1377	(esd (electrostatic adj discharge)) same impedance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 09:18
S46	175	(esd (electrostatic adj discharge)) same impedance same (size length dimension)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 09:18
S47	22	(esd (electrostatic adj discharge)) same impedance same (size length dimension) with (lead wire trace)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:24
S48	1745	361/111.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 10:25
S49	1668	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 12:06
S50	1	10/783,059	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 10:33
S51	0	esd and protect\$3 and channel near impedance near (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:30

EAST Search History

S52	0	esd and channel near impedance near (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:31
S53	21	esd and impedance near (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:42
S54	1	10/633,544	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:47
S55	4	"6,066,916"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:49
S56	14	"6,153,913"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 11:49
S57	35	esd and diode with channel near (length width)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:07
S58	22	esd and diode with channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:21
S59	26	esd and diode with channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:21

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S60	881	esd and channel with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:21
S61	514	esd and channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:21
S62	22	esd and diode with channel near width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:22
S63	0	esd and diode with channel near width near (wider larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:22
S64	0	esd and diode with channel with width near (wider larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:23
S65	16	esd and channel with width near (wider larger)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 15:23
S66	10	("5019001" "5019002" "5130829" "5220443" "5373377" "5384266" "5448095" "5486716" "5497146" "5504348").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/03/20 15:59
S67	17	("5798534").URPN.	USPAT	OR	ON	2007/03/20 16:19
S68	1	10/783,059	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:48

EAST Search History

S69	0	esd and trace near length near compensat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:49
S70	3	esd and trace with length with compensat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:50
S71	573	esd and resistance with (larger wider)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:52
S72	104	esd and device with resistance with (larger wider)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:52
S73	93	esd and device with resistance with larger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:52
S74	154	esd and trace with length	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:53
S75	3	esd and trace with length with compensat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:53
S76	31	esd and trace with length with (different vary\$3 longer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:57

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S77	0	esd same trace with length with (different vary\$3 longer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:54
S78	18	esd and trace with length with resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 10:59
S79	1	esd same trace with length with resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:03
S80	19	"5,798,534"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:05
S81	7	"5,798,534" and resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:04
S82	0	"5,798,534" and resistance with (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:05
S83	786	esd and resistance with (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:06
S84	271	esd same resistance with (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:06

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S85	48	esd same resistance near (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:06
S86	35	esd near9 resistance near (larger smaller)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 11:42
S87	38	"5,497,146"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:13
S88	72	esd and channel near width with resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 12:13
S89	7	esd and channel near width near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 13:09
S90	0	"10633544"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 13:10
S91	1	"10/633,544"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 14:36
S92	1	10/633,544	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 14:51

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S93	1	10/783,059	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:16
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